

TOSHIBA

0.14 μ m CMOS ASIC TC260 Family

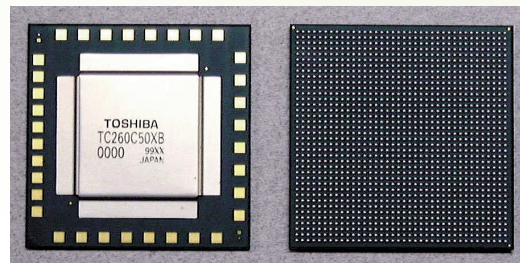
PRODUCT GUIDE

SLI ASIC for High-Function, Low-Power Applications

TC260 Family

The TC260 family of System-Level Integration (SLI) ASICs are designed for applications needing the highest performance with the smallest die size and lowest power. The family includes TC260C cell-based ICs for best density and TC260E embedded arrays for fast turnaround time. Using a highly sophisticated transistor design, the TC260 achieves an effective channel length of 0.12 μm (0.14 μm -drawn), with 125 kgates per mm^2 . Toshiba's TC260 technology is 30% faster than the previous generation technology, and it also cuts power dissipation by 80% while increasing the logic density by 3.4 times.

Toshiba offers two types of embedded DRAM, one targeted for high bandwidth, the other for low latency with SRAM-like ease of use. The embedded DRAM cores are based on Toshiba's leading trench capacitor technology,



which permits mixing of logic and DRAM without compromising logic performance. Toshiba's IP library includes a full line of MIPS-based RISC, and cores that serve the multimedia, networking, communications, data processing, computing, digital consumer electronics and mobile applications.

Toshiba delivers proven cell libraries, design methodologies and tools to help reduce design time and iterations. Encompassing Toshiba's tool suite are hardware/software coverification, hierarchical layout, near-zero clock skew management, etc.

Features of the TC260 Family

Ultra-High Density and Ultra-Low Power

Fabricated using a 0.14 μm -drawn ($L_{\text{eff}}=0.12 \mu\text{m}$) CMOS process and 6 levels of metal, the TC260 provides three major advantages over the previous 0.25- μm TC240 technology:

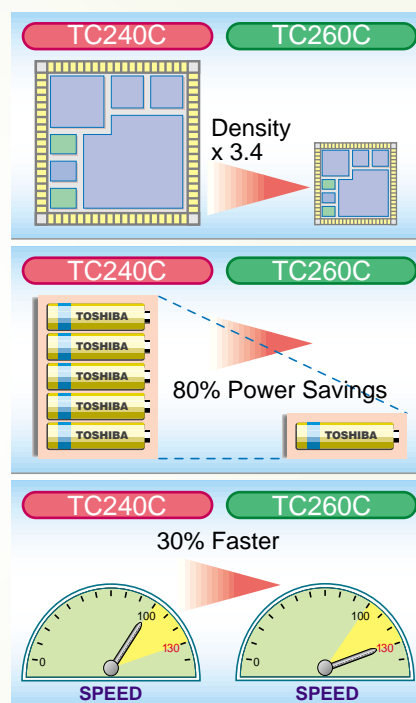
- x3.4 improvement in logic density
- 80% power savings per gate
- 30% reduction in gate delay

Embedded DRAM

Embedded DRAM offers a significant advantage over off-chip memory solutions that stems from the flexibility of choosing wide memory buses and lower power dissipation due to lower capacitance on-chip connections. Since the embedded DRAM cores are based on Toshiba's leading trench capacitor technology, logic performance is not degraded.

High-Speed and High-Density SRAM Cells

The TC260 family offers two types of SRAM cells. The high-speed type can go as high as 500 MHz; the high-density type requires approximately 1/3 the chip's real estate of conventional SRAMs.



General Product Specifications

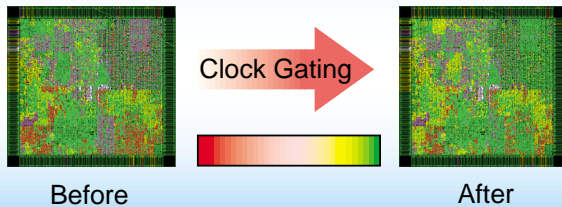
Gate Length	CMOS process, 6-layer Al
Power Supply	VDD = 1.5 V (Core); 2.5 V or 3.3V (I/O)
Gate Delay (F/O=1, CIVX2 Cell)	18 ps (standard type), 15 ps (high-speed type) * Two types of transistors are available with different threshold voltages.
Gate Density	125 kgates/ mm^2 (TC260C cell-based ICs)
Power Dissipation	15 nW/MHz/gate (CIVXL cell)

Low-Power Technology Front-End and Back-End Optimizations

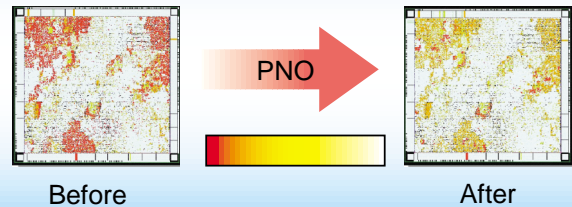
With the ever growing complexity of deep-submicron designs, the need for low-power design is increasingly acute. Clock gating is a common power reduction technique. Toshiba's new design methodologies automate the process of inserting clock gating logic in a design. You can embrace clock gating up front as early as at RTL. Additionally, during physical layout, Toshiba's circuit

optimization tool, PNO, employs unique techniques to create the lowest power implementation permitted by the timing constraints on a design. For best results, cell libraries contain several functionally-equivalent cells differing in drive strength, allowing the optimal tuning of performance and power.

Effectiveness of Clock Gating



Effectiveness of PNO



DRAM Cores and Application-Specific IP

Toshiba supports an ever-growing selection of IP cores. These range from general cells such as RISC processors and DRAMs through application-specific IP.

MPU	: TX System RISC
Protocol Control	: IEEE1394, IEEE1284, PCI, USB, IrDA, PCMCIA
High-Performance I/O	: PCI, AGP, USB, LVDS
Multimedia	: JPEG, MPEG, Smart Media™
Networking	: Ethernet Controller
Analog cores	: ADC, DAC, PLL
Memory	: DRAM, SRAM, ROM

SD Type (High-bandwidth SDRAM)

Maximum clock rate: 200 MHz
Maximum data rate: 6.4 GB/s
Random access cycle: 48 ns
Size: 2 to 32 Mb

FA Type (Fast-access SDRAM with SRAM-like easy of use)

Latency: < 2 cycles
Random access cycle: 30 ns
Size: 1 to 4 Mb

Benefits of Embedded DRAM Cores

1) Flexibility in configuring the DRAM cells based on application requirements; 2) high bandwidth due to wide and fast memory buses; 3) faster access time than discrete DRAM components; 4) lower power dissipation due to lower-

capacitance on-chip connections; and lower switching noise on data bus between memory and logic. The TC260 offers two types of DRAM cores, SD type for high bandwidth and FA type for low latency.

Packaging

Toshiba's comprehensive packaging options include electrically enhanced, 4-layer EPBGAs (352 to 576 pins), high-performance, high-pin-count PBGA[FC]s (>800 pins), chip-scale PFBGAs with <15mmX15mm body size (109

to 265 pins) and fine-pitch TBGAs (256 to 768 pins). Toshiba also supports a wide range of cost/performance requirements with QFPs having 44 to 304 pins.

EDA Tools

To ease the burden of designing multi-million-gate SLI ASICs, Toshiba supports many industry-standard EDA tools for logic synthesis, sign-off simulation, static timing analysis, design-for-test, formal verification, floorplanning and emulation. Such back-end features as near-zero

clock skew management, multi-layer routing and timing/power optimization are designed to minimize layout-related design iterations in order to help reduce development time and improve market responsiveness.

**Toshiba America
Electronic Components, Inc.**
Headquarters-Irvine, CA

9775 Toledo Way, Irvine, CA 92618, U.S.A.
Tel: (949)455-2000 Fax: (949)859-3963

Boulder, CO

3100 Arapahoe Avenue, Ste. 500,
Boulder, CO 80303, U.S.A.
Tel: (303)442-3801 Fax: (303)442-7216

Boynton Beach, FL(Orlando)

11924 W. Forest Hill Blvd., Ste. 22-337,
Boynton Beach, FL 33414, U.S.A.
Tel: (561)374-6193 Fax: (561)374-6194

Deerfield, IL(Chicago)

One Pkwy., North, Suite 500, Deerfield,
IL 60015-2547, U.S.A.
Tel: (847)945-1500 Fax: (847)945-1044

Duluth, GA(Atlanta)

3700 Crestwood Parkway, Ste. 460,
Duluth, GA 30096, U.S.A.
Tel: (770)931-3363 Fax: (770)931-7602

Edison, NJ

2035 Lincoln Hwy. Ste. #3000, Edison
NJ 08817, U.S.A.
Tel: (732)248-8070 Fax: (732)248-8030

Orange County, CA

2 Venture Plaza, #500 Irvine, CA 92618, U.S.A.
Tel: (949)453-0224 Fax: (949)453-0125

Portland, OR

1700 NW 167th Place, #240,
Beaverton, OR 97006, U.S.A.
Tel: (503)629-0818 Fax: (503)629-0827

Richardson, TX(Dallas)

777 East Campbell Rd., Suite 650, Richardson,
TX 75081, U.S.A.
Tel: (972)480-0470 Fax: (972)235-4114

San Jose Engineering Center, CA

1060 Rincon Circle, San Jose, CA 95131, U.S.A.
Tel: (408)526-2400 Fax: (408)526-2410

Wakefield, MA(Boston)

401 Edgewater Place, Suite #360, Wakefield,
MA 01880-6229, U.S.A.
Tel: (781)224-0074 Fax: (781)224-1095

Toshiba Electronics Europe GmbH
Düsseldorf Head Office

Hansaallee 181, D-40549 Düsseldorf
Germany
Tel: (0211)5296-0 Fax: (0211)5296-400

München Office

Büro München Hofmannstrasse 52,
D-81378, München, Germany
Tel: (089)748595-0 Fax: (089)748595-42

Toshiba Electronics France SARL

Immeuble Robert Schumann 3 Rue de Rome,
F-93561, Rosny-Sous-Bois, Cedex, France
Tel: (1)48-12-48-12 Fax: (1)48-94-51-15

Toshiba Electronics Italiana S.R.L.

Centro Direzionale Colleoni
Palazzo Perseo Ingr. 2-Piano 6,
Via Paracelso n.12,
1-20041 Agrate Brianza Milan, Italy
Tel: (039)68701 Fax: (039)6870205

Toshiba Electronics España, S.A.

Parque Empresarial San Fernando Edificio Europa,
1ª Planta, ES-28831 Madrid, Spain
Tel: (91)660-6700 Fax: (91)660-6799

Toshiba Electronics(UK) Limited

Riverside Way, Camberley Surrey,
GU15 3YA, U.K.
Tel: (01276)69-4600 Fax: (01276)69-4800

Toshiba Electronics Scandinavia AB

Gustavslundsvägen 12, 2nd Floor
S-161 15 Bromma, Sweden
Tel: (08)704-0900 Fax: (08)80-8459

**Toshiba Electronics Asia
(Singapore) Pte. Ltd.**

Singapore Head Office
438B Alexandra Road, #06-08/12 Alexandra
Technopark, Singapore 119968
Tel: (278)5252 Fax: (271)5155, (270)6056

Bangkok Office

135 Moo 5 Bangkadi Industrial Park, Tivanon Rd.,
Bangkadi Amphur Muang Pathumthani, Bangkok,
12000, Thailand
Tel: (02)501-1635 Fax: (02)501-1638

**Toshiba Electronics Trading
(Malaysia)Sdn. Bhd.**

Kuala Lumpur Head Office
Suite W1203, Wisma Consplant, No.2,
Jalan SS 16/4, Subang Jaya, 47500 Petaling Jaya,
Selangor Darul Ehsan, Malaysia
Tel: (3)731-6311 Fax: (3)731-6307

Penang Office

Suite 13-1, 13th Floor, Menard Penang Garden,
42-A, Jalan Sultan Ahmad Shah,
100 50 Penang, Malaysia
Tel: 4-226-8523 Fax: 4-226-8515

Toshiba Electronics Philippines, Inc.

26th Floor, Citibank Tower, Valero Street, Makati,
Manila, Philippines
Tel: (02)750-5510 Fax: (02)750-5511

Toshiba Electronics Asia, Ltd.
Hong Kong Head Office

Level 11, Top Glory Insurance Building, Grand Century
Place, No.193, Prince Edward Road West,
Mong Kok, Kowloon, Hong Kong
Tel: 2375-6111 Fax: 2375-0969

Beijing Office

Rm 714, Beijing Fortune Building,
No.5 Dong San Huan Bei-Lu, Chao Yang District,
Beijing, 100004, China
Tel: (010)6590-8795 Fax: (010)6590-8791

Chengdu Office

Unit F, 18th Floor, New Times Plaza, 42 Wenwu Road,
Xinhua Avenue, Chengdu, 610017, China
Tel: (028)675-1773 Fax: (028)675-1065

Shenzhen Office

Rm 3010-3012, Office Tower Shun Hing Square,
Di Wang Commercial Centre, 333 ShenNan
East Road, Shenzhen, 518008, China
Tel: (0755)246-1582 Fax: (0755)246-1581

Toshiba Electronics Korea Corporation
Seoul Head Office

14/F, KEC B/D, 257-7 Yangjae-Dong,
Seocho-ku, Seoul, Korea
Tel: (02)589-4334 Fax: (02)589-4302

Kumi Office

6/F, Ssangyong Investment Securities B/D,
56 Songjung-Dong, Kumi City
Kyeongbuk, Korea
Tel: (82)546-456-7613 Fax: (82)546-456-7617

**Toshiba Technology Development
(Shanghai) Co., Ltd.**

23F, Shanghai Senmao International Building, 101
Yin Cheng East Road, Pudong New Area, Shanghai,
200120, China
Tel: (021)6841-0666 Fax: (021)6841-5002

**Tsurong Xiamen Xiangyu Trading
Co., Ltd.**

8N, Xiamen SEZ Bonded Goods Market Building,
Xiamen, Fujian, 361006, China
Tel: (0592)562-3798 Fax: (0592)562-3799

**Toshiba Electronics Taiwan
Corporation**
Taipei Head Office

17F, Union Enterprise Plaza Bldg. 109
Min Sheng East Rd., Section 3, 0446 Taipei,
Taiwan R.O.C.
Tel: (02)514-9988 Fax: (02)514-7892

Kaohsiung Office

16F-A, Chung-Cheng Bldg., Chung-Cheng 3Rd.,
80027, Kaohsiung, Taiwan R.O.C.
Tel: (07)222-0826 Fax: (07)223-0046

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In Touch with Tomorrow
TOSHIBA

TOSHIBA CORPORATION
Electronic Devices Sales & Marketing Group

1-1, Shibaura 1-chome, Minato-ku, Tokyo, 105-8001, Japan
Tel: (03)3457-3405 Fax: (03)5444-9431